

C1650-30

Near Infrared LED CHIP

<Specifications>

Commodity Type and Physical Characteristics	
Material	InGaAsP/InP(DDH)
Top Side P(anode)side	Au Alloy
Bottom Side N(cathode)side	Au Alloy
Electrode Pattern	Fig.1
Chip Size	Fig.2
Chip Thickness	Fig.2
Emission Area	Fig.2

Electro-Optical Characteristics [Ta=25°C]							
Item	Symbol	Condition	Min.	Typ.	Max.	Unit	
Forward Voltage	Vf	IF=20mA		0.78	1.2	V	
		IF=50mA		0.85	1.3		
Reverse Current	IR	VR=3V			10	uA	
Power Intensity	PO	IF=20mA		0.75		mW	
		IF=50mA		1.50			
Wavelength	Peak	λP	IF=50mA	1600	1650	1700	nm
	Centroid			λC		1615	
Spectral Radiation Bandwidth	Δλ	IF=50mA		130		nm	
Rise Time	tr	IF=20mA		40		ns	
Fall Time	tf	IF=20mA		40		ns	

Die shall be mounted on TO-18 gold header without resin coated.

[Unit:um]

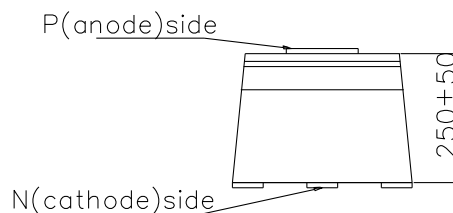
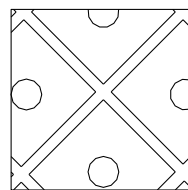
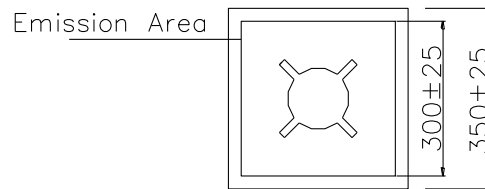
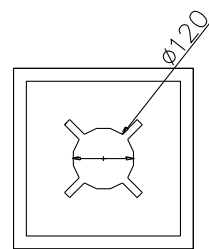


Fig.1 Electrode Pattern

Fig.2 Chip Size and Emission Area